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Transport properties of a quantum wire: the role of extended time-dependent impurities

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We study the transport properties of a quantum wire, described by the Tomonaga-Luttinger model, in the presence of a backscattering potential provided by several extended time-dependent impurities (barriers). Employing the Büttiker-Landauer approach, we first consider the scattering of noninteracting electrons ($g = 1$) by a rectangular-like barrier and find an exact solution for the backscattering current, as well as a perturbative solution for a weak static potential with an arbitrary shape. We then include electron-electron interactions and use the Keldysh formalism combined with the bosonization technique to study oscillating extended barriers. We show that the backscattering current off time-dependent impurities can be expressed in terms of the current for the corresponding static barrier. Then we determine the backscattering current for a static extended potential, which, in the limit of noninteracting electrons ($g = 1$), coincides with the result obtained using the Büttiker-Landauer formalism. In particular, we find that the conductance can be increased beyond its quantized value in the whole range of repulsive interactions $0 < g < 1$ already in the case of a single oscillating extended impurity, in contrast to the case of a point-like impurity, where this phenomenon occurs only for $0 < g < 1/2$.

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I. INTRODUCTION

The electronic transport in mesoscopic systems has been intensively studied during the last decades.[1,2] The conductance of mesoscopic wires is usually computed using the Büttiker-Landauer formalism,[3] which accounts for the quantum mechanical nature of transmission and reflection through impurities and works well for Fermi liquids.

Recent advances in nanotechnology, together with the discovery of carbon nanotubes[4,5] have enabled the fabrication of extremely narrow wires, which are basically one-dimensional. Because the electron-electron interactions become essential in 1D, these quantum wires exhibit Luttinger liquid behavior, i.e., they have bosonic collective excitations, instead of the usual fermionic quasi-particles present in conventional Fermi liquids.[6]

The role played by impurities in a Luttinger liquid depends crucially on the nature of the interactions. In path-breaking papers, Kane and Fisher[7,8] showed that the impurity barrier is irrelevant if the electrons have attractive interactions ($g > 1$), but it cuts the wire into two pieces if they interact repulsively ($g < 1$). For the noninteracting case ($g = 1$) the barrier is a marginal perturbation, i.e., one can have both, transmission and reflection.

For the case of two barriers, contrarily to the expectation, it is possible to have transmission even in the presence of repulsive interactions ($g < 1$) because quasi-bound-states can form between the barriers, which lead to resonant transmission.[9]

The vast majority of cases discussed in the literature concerning transport in Luttinger liquids involve *static point-like* impurity barriers. Recently, the case of *dynamical point-like* impurities was addressed.[10,11,12,13,14] Feldman and Gefen[12] have shown that in the presence of one impurity oscillating with frequency Ω, the backscattering current may change sign and the conductance of a single-mode Luttinger liquid with strong repulsive interactions ($g < 1/2$) may become *larger* than the quantum of conductance $G_0 = e^2/h$. We have generalized their results and shown that in the presence of several impurities this phenomenon occurs even for $1/2 < g < 1$.[14] In fact, we have found that the dc-current can always be expressed in terms of the backscattering current off a static impurity. The effect of the impurity frequency Ω is solely to split the energy modes into $\omega_0 + \Omega$ and $\omega_0 - \Omega$, where $\omega_0 = eV/\hbar$ denotes the Josephson frequency, associated with the external voltage V. Hence, within first order perturbation theory, several point-like impurities oscillating in phase may lead to an increase of the conductance, in a certain range of parameters, but in the entire regime of repulsive interactions $0 < g < 1$.[14]

After having understood the role of *time-dependent point-like impurities*, the remaining task is to investigate transport through *extended time-dependent* impurities.[15] This is precisely the aim of this paper. The coherent transport properties of multimode quantum channels in the presence of Gaussian-like scatterers was considered recently.[16] In addition, the tunneling current between two counterpropagating edge modes described by chiral Luttinger liquids was calculated for the case when tunneling takes place along an extended region.[17]

In this work we evaluate the backscattering current off *several time-dependent extended impurities* in an otherwise perfect Luttinger liquid, in the presence of repulsive electron-electron interactions. We start in Section II with a single static extended impurity in the noninteracting limit ($g = 1$), which can be solved using the Büttiker-Landauer formalism,[3] and then we generalize the results for the case of an arbitrary static potential. In Section III we include interactions among the electrons and study the problem using the Keldysh formalism. Within first order perturbation theory, we first derive a general expression for the backscattering current in the presence of several time-dependent extended impurities and then we concentrate on a typical example, namely, the case of one impurity, to illustrate the main results. Finally, we compare our findings obtained within perturbation theory in the limit of noninteracting electrons ($g = 1$) with the exact results derived in the framework of the Büttiker-Landauer formalism and show a perfect agreement between them. Our conclusions are presented in Section IV.

II. NON-INTERACTING ELECTRONS ($g = 1$) IN AN EXTENDED BACKSCATTERING POTENTIAL

A. The Model

We start by studying the simplest case, namely, non-interacting electrons in 1D in the presence of a backscattering potential. The Hamiltonian of the model reads $H = H_0 + H_{imp}$, where

$$\begin{aligned} H_0 &= -i\hbar v_F \int dx(\psi_R^\dagger \partial_x \psi_R - \psi_L^\dagger \partial_x \psi_L), \qquad (1) \\ H_{imp} &= \int dx(\psi_R^\dagger \psi_L + \psi_L^\dagger \psi_R) W(x,t). \end{aligned}$$

Here $\psi_{R/L}$ are fermionic fields corresponding to the right/left moving electrons and $W(x,t)$ stands for the backscattering potential. We also further set the Planck constant $\hbar = 1$ and the Fermi velocity $v_F = 1$. The equations of motion then read

$$\begin{aligned} (\partial_t + \partial_x)\psi_R + iW(x,t)\psi_L &= 0, \qquad (2) \\ (\partial_t - \partial_x)\psi_L + iW(x,t)\psi_R &= 0. \end{aligned}$$

For a static backscattering potential, $W(x,t) = W(x)$, the solutions of the above equations of motion have a stationary form, $\psi_{R/L}(x,t) = \psi_{R/L}(x)e^{-i\omega t}$. The fermionic fields $\psi_{R/L}$ then obey the following equation of motion

$$\left(\begin{array}{cc} \omega + i\partial_x & -W(x) \\ -W(x) & \omega - i\partial_x \end{array} \right) \psi(x) = 0, \qquad (3)$$

where we introduced a "spinor" notation

$$\psi \equiv \left(\begin{array}{c} \psi_R \\ \psi_L \end{array} \right). \qquad (4)$$

In the following we concentrate on some particular examples for which an analytical solution can be obtained.

B. Single static rectangular-like barrier

Let us begin by considering a static rectangular-like potential barrier of width L and height W,

$$W(x) = W[\Theta(x + L/2) - \Theta(x - L/2)], \qquad (5)$$

where $\Theta(x)$ is the Heavyside theta-function. The solution of the stationary equation of motion (3) may be sought in the form

$$\begin{aligned} \psi_R(x) &= \psi_R^- e^{-ikx} + \psi_R^0 e^{ikx}, \qquad (6) \\ \psi_L(x) &= \psi_L^0 e^{-ikx} + \psi_L^- e^{ikx}. \end{aligned}$$

Substitution of the ansatz (6) into the equations of motion (3) yields

$$\psi_L^- = \frac{W(x)}{\omega + k}\psi_R^0, \qquad \psi_R^- = \frac{W(x)}{\omega + k}\psi_L^0, \qquad (7)$$

with $\omega^2 = [W(x)]^2 + k^2$. We now consider the region $[-L/2, L/2]$ and require both functions $\psi_L(x)$ and $\psi_R(x)$ to be continuous at the points $x = \pm L/2$. For the point $x = -L/2$ we have

$$\begin{aligned} \psi_R(-L/2) &= \psi_R^0 e^{-ikL/2} + \frac{W}{\omega + k}\psi_L^0 e^{ikL/2}, \qquad (8) \\ \psi_L(-L/2) &= \frac{W}{\omega + k}\psi_R^0 e^{-ikL/2} + \psi_L^0 e^{ikL/2}, \end{aligned}$$

where $k = \sqrt{\omega^2 - W^2}$, and for the point $x = L/2$ the expressions are similar. Introducing the matrices

$$B = \left(\begin{array}{cc} 1 & \frac{W}{\omega+k} \\ \frac{W}{\omega+k} & 1 \end{array} \right) \qquad (9)$$

and

$$P = \left(\begin{array}{cc} e^{ikL/2} & 0 \\ 0 & e^{-ikL/2} \end{array} \right), \qquad (10)$$

the continuity conditions can be written in a simple form

$$\psi(-L/2) = BP^\dagger \psi^0, \qquad \psi(L/2) = BP\psi^0. \qquad (11)$$

The above equations then yield

$$\psi(L/2) = M\psi(-L/2), \qquad M = BP^2B^{-1}, \qquad (12)$$

where M is the transmission matrix, which gives the transformation from the states on the left of the barrier, $\psi_{R/L}(-L/2)$, to the states on the right of the barrier $\psi_{R/L}(L/2)$,

$$M = \left(\begin{array}{cc} \cos(kL) + i\frac{\omega}{k}\sin(kL) & -i\frac{W}{k}\sin(kL) \\ i\frac{W}{k}\sin(kL) & \cos(kL) - i\frac{\omega}{k}\sin(kL) \end{array} \right). \qquad (13)$$

Let us observe that $M^\dagger \sigma_3 M = \sigma_3$, and therefore $\bar{\psi}\psi$ is a constant, where $\bar{\psi} = \psi^\dagger \sigma_3$ is the Dirac conjugate. This is a consequence of charge conservation and holds for any transmission matrix, since an arbitrary backscattering potential can always be represented as a set of (infinitely narrow) rectangular potentials with different amplitudes. Therefore, the transmission matrix $M \in SU(1,1)$ can be always written in the form

$$M = \begin{pmatrix} s & r^* \\ r & s^* \end{pmatrix}. \tag{14}$$

A more elegant derivation of Eq. (13) using results of the Lie group theory is presented in the Appendix. The transmission matrix given by Eq. (14) is related to the scattering matrix, S, which gives the transformation from the incoming modes $\psi_R(-L/2), \psi_L(L/2)$ to the outgoing modes $\psi_R(L/2), \psi_L(-L/2)$. In terms of the transmission matrix elements, the latter reads

$$S = \frac{s}{|s|} \begin{pmatrix} 1/|s| & r^*/|s| \\ -r/|s| & 1/|s| \end{pmatrix}. \tag{15}$$

Let us now calculate the transmission coefficient for the right moving particles using Eq. (12). In that case, we have

$$\begin{pmatrix} \psi_R(L/2) \\ 0 \end{pmatrix} = M \begin{pmatrix} \psi_R(-L/2) \\ \psi_L(-L/2) \end{pmatrix}, \tag{16}$$

with the transmission matrix M given by Eq. (13). The transmission coefficient may be then promptly found from the previous equation

$$T \equiv \left| \frac{\psi_R(L/2)}{\psi_R(-L/2)} \right|^2 = \frac{1}{|s|^2} = \frac{1}{1+|r|^2}, \tag{17}$$

Using the explicit form of the transmission matrix, given by Eq. (13), we obtain for $\omega^2 \geq W^2$

$$T(\omega) = \left[1 + \frac{W^2}{\omega^2 - W^2} \sin^2(\sqrt{\omega^2 - W^2} L) \right]^{-1} \tag{18}$$

and for $\omega^2 < W^2$

$$T(\omega) = \left[1 + \frac{W^2}{W^2 - \omega^2} \sinh^2(\sqrt{W^2 - \omega^2} L) \right]^{-1}. \tag{19}$$

An analogous calculation shows that the transmission coefficient for the left moving particles is the same as for the right moving ones. We can now find the backscattering current using the Landauer formula[3] and choosing the left and right reservoirs to be symmetric. We use the subscript "*st*" to denote the backscattering current off a *static* impurity to distinguish it from the backscattering current originating from *time-dependent barriers*, which is considered in the next section. The current then reads

$$I_{st} = e \int_{-\infty}^{\infty} \frac{d\omega}{2\pi} [n^R(\omega) - n^L(\omega)][T(\omega) - 1], \tag{20}$$

where $n^{R/L}(\omega)$ are the occupation numbers of the right/left movers, given by the Fermi distribution function

$$n^{R/L}(\omega) = \frac{1}{e^{\beta(\omega - \omega_F \mp \omega_0/2)} + 1}. \tag{21}$$

Here, $\omega_0 = eV$ is the Josephson frequency related to the applied bias voltage V and ω_F is the Fermi energy (recall that $\hbar$=1). We have to distinguish the two cases given by Eqs. (18) and (19), since if $\omega^2 < W^2$ the momentum k becomes imaginary and transport occurs then only via tunnelling. In other words, the presence of backscattering opens a gap in the energy spectrum of the fermions from $\omega_F - W$ to $\omega_F + W$. Substituting Eq. (18) into Eq. (20) and keeping only the lowest order terms in W, we find the "static" backscattering current

$$I_{st} = -\frac{eW^2}{2\pi} \int_{-\infty}^{\infty} d\omega \frac{\sin^2(\omega L)}{\omega^2} [n^R(\omega) - n^L(\omega)]. \tag{22}$$

At zero temperature ($T = 0$) and $\omega_F = 0$ the above expression simplifies to

$$I_{st} = -\frac{2eW^2 L}{\pi} \int_0^{L\omega_0} dy \frac{\sin^2(y/2)}{y^2}. \tag{23}$$

The backscattering currents at a finite and zero temperature, given by Eqs. (22) and (23), are plotted, respectively, in the upper and the lower panel of Fig. 1. In both cases the current I_{st} is represented in units of eW^2L and the Josephson frequency is in units of $1/L$. Inspection of Fig. 1 shows that in the region $L\omega_0 < 2$, the current I_{st} for scattering off an extended impurity (solid line) is almost indistinguishable from the backscattering current of a point-like impurity represented by a barrier $\tilde{W}(x) = WL\delta(x)$ (dashed line). However, in the region $L\omega_0 > 2$ the difference becomes drastic, since the backscattering current off a point-like impurity continues to decrease linearly, whereas for the extended impurity, the current saturates at the value $I_{bs} = -eW^2L/2$.

C. Arbitrary static potential

Let us now consider noninteracting electrons backscattered off a static potential $W(x)$ localized in the interval $0 \leq x \leq y$ with the corresponding transmission matrix $M(y)$. In order to find the dependence of the transmission matrix on the scattering potential, let us add to the existing barrier an infinitesimally thin part with the height $W(y + dy)$. In this case the transmission matrix at the point $y + dy$ is $M(y + dy) = M(y) + dM$, where $dM = i\mathcal{T}M dy$ (see Appendix). After performing a matrix multiplication, we find the following differential equations

$$\begin{aligned} ds &= i[\omega s - W(y) r] dy, \\ dr &= i[W(y) s - \omega r] dy. \end{aligned} \tag{24}$$

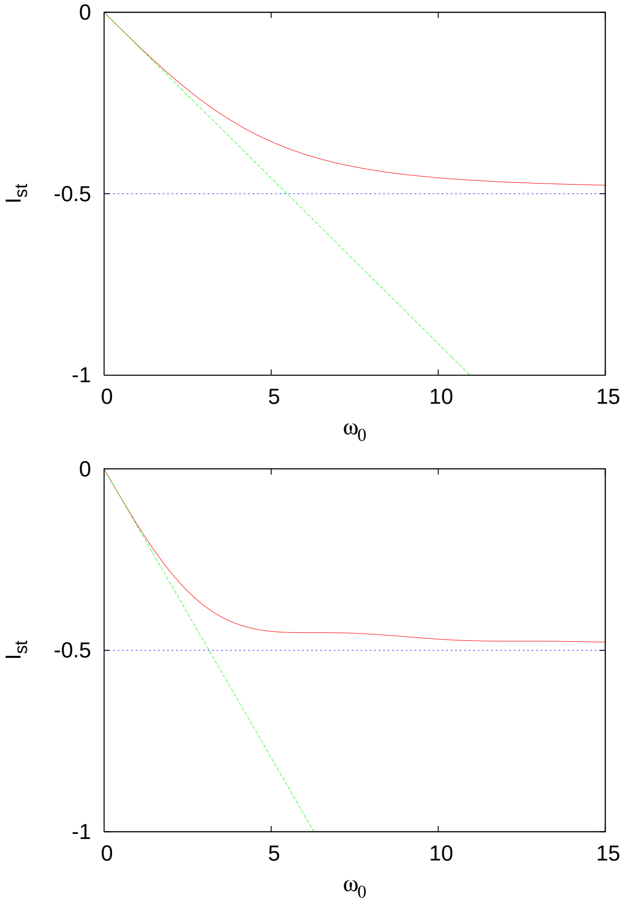

Figure 1: (color online) I_{st} versus ω_0 for noninteracting electrons ($g = 1$) in the presence of a point-like (dashed line) or an extended impurity (solid line). The asymptotic behavior for the latter, $I_{st}(\omega \to \infty) \to -1/2$, is represented by dotted lines. The current is plotted in units of eW^2L and the frequency is in units of $1/L$. Upper panel: $T = 1$; lower panel: $T = 0$.

If the potential is weak, $W(y) \ll \omega$, then to the lowest order in perturbation expansion $r = \mathcal{O}(W/\omega)$. After neglecting terms $\mathcal{O}(r^3)$, we obtain

$$dr(y) = i[W(y)e^{i\omega y} - \omega r(y)]dy. \tag{25}$$

This is a linear inhomogeneous differential equation of the first order with solution of the form

$$r(y) = ie^{-i\omega y}\int_0^y dxW(x)e^{i2\omega x}. \tag{26}$$

Then, it follows straightforwardly that

$$|r|^2 = \int dx_1 \int dx_2 W(x_1)W(x_2)\cos[2\omega(x_1 - x_2)]. \tag{27}$$

On the other hand, since $|r|^2 \ll 1$, the transmission coefficient becomes

$$T(\omega) - 1 = \frac{1}{1 + |r|^2} - 1 = -|r|^2, \tag{28}$$

and the backscattering current at finite temperatures then reads

$$I_{st} = -e\int_{-\infty}^{\infty}\frac{d\omega}{2\pi}|r|^2[n^R(\omega) - n^L(\omega)]. \tag{29}$$

Consequently, we find that

$$\begin{aligned}&\frac{\delta^2}{\delta W(x_1)\delta W(x_2)}I_{st}|_{W=0} = \qquad (30)\\ &-e\int_{-\infty}^{\infty}\frac{d\omega}{\pi}\cos[2\omega(x_1 - x_2)][n^R(\omega) - n^L(\omega)].\end{aligned}$$

Since

$$\int_{-\infty}^{\infty} dy\cos(y)[n^R(y/2l) - n^L(y/2l)] = 4\pi Tl\frac{\sin(\omega_0 l)\cos(2\omega_F l)}{\sinh(2\pi Tl)},$$

we eventually obtain that

$$\begin{aligned}&\frac{\delta^2 I_{st}}{\delta W(x_1)\delta W(x_2)}|_{W=0} = \qquad (31)\\ &-2eT\frac{\cos[2\omega_F(x_1 - x_2)]\sin[\omega_0(x_1 - x_2)]}{\sinh[2T\pi(x_1 - x_2)]}.\end{aligned}$$

As we will see later, Eq. (31) will allow us to connect the results obtained within perturbation theory in the bosonization formalism with the ones derived in the framework of the Büttiker-Landauer approach, for an arbitrary (but weak) extended impurity barrier, in the limit of noninteracting electrons ($g = 1$).

III. INTERACTING ELECTRONS

A. Several time-dependent extended impurities

In this section we consider a one-dimensional quantum wire with spinless interacting electrons backscattered by a *time-dependent* potential $W(x, t)$. The Hamiltonian of the model, including the electron-electron interaction, reads[12,18,19]

$$\begin{aligned} H &= \int dx\left\{-i(\psi_R^\dagger\partial_x\psi_R - \psi_L^\dagger\partial_x\psi_L) + U(\psi_R^\dagger\psi_R + \psi_L^\dagger\psi_L)^2\right. \\ &+ \left. W(x,t)\left[\psi_L^\dagger\psi_R e^{i\omega_0 t + i2k_F x} + H.c.\right]\right\}, \end{aligned} \tag{32}$$

where U is the interaction strength. In the next step, we consider a discretized backscattering potential $W(x, t)$ composed of several point-like time-dependent impurities located at positions x_p, $p = 1, ..., N$, such that

$$\lim_{\Delta x_p \to 0+}\sum_{p=1}^{N} W(x_p, t)\Delta x_p = \int W(x, t)dx. \tag{33}$$

We now use the bosonization technique, which relates the fermionic fields, $\psi_{R/L}$, with the corresponding bosonic fields, $\Phi_{R/L}$, through $\psi_{R/L} = \alpha\eta e^{\pm i\sqrt{g}\Phi_{R/L}}$.

Here, α is a normalization factor, η is a fermionic operator, and $g = \sqrt{\pi/(\pi + 2U)}$ (recall $v_F = 1$) is the coupling constant in the bosonic theory. The action corresponding to the Hamiltonian (32) then reads[12,14,18,19,20,21]

$$\begin{aligned} S &= \int dt dx \left\{ \frac{1}{8\pi} \left[(\partial_t \Phi)^2 - (\partial_x \Phi)^2 \right] \right. \qquad (34) \\ &- \left. \sum_p \delta(x - x_p) V_p(t) \left(e^{i\sqrt{g}\Phi(t,x_p)} e^{i\omega_0 t} + H.c. \right) \right\}, \end{aligned}$$

where $V_p(t) \equiv W(x_p,t) e^{i2k_F x_p} \Delta x_p / 2\pi$ and $\Phi \equiv \Phi_R + \Phi_L$. Using the approach developed in Refs. [14] and [18], we find that, to the lowest order in V, the backscattering current reads

$$I_{bs}(\omega_0,t) = C \sum_{k,j} \int_{|x_k - x_j|}^{\infty} \frac{d\tau \sin(\omega_0 \tau) V_k^*(t-\tau) V_j(t)}{|\tau^2 - (x_k - x_j)^2|^g} + H.c., \tag{35}$$

where $C = -2e\sin(\pi g)$. The most general case should involve a spatially varying impurity potential, with an arbitrary shape. In order to account for this more general situation, we take the continuum limit in Eq. (35) by setting the number of impurities $N \to \infty$ and the distance between the impurities $\Delta x_p \to 0$. Eq. (35) then acquires the form

$$\begin{aligned} I_{bs}(\omega_0,t) = -e\frac{\sin(\pi g)}{\pi^2} \int\int dx_1 dx_2 \int_{|x_1 - x_2|}^{\infty} d\tau \\ \frac{\sin(\omega_0 \tau) \cos[2k_F(x_1 - x_2)] W(x_1, t-\tau) W(x_2, t)}{|\tau^2 - (x_1 - x_2)^2|^g}. \qquad (36) \end{aligned}$$

Eq. (36) is a very important result of our paper because it allows us to evaluate the backscattering current for any set of time-dependent extended impurities, described by any arbitrary function $W(x,t)$.

We can progress further in the analytical calculation of some specific examples by introducing a simplifying assumption, namely, that the impurity potential is a periodic function of time, $W(x,t) = W(x)\cos(\Omega t)$. We have shown in Ref. 14 that the dc component of the backscattering current generated by a set of dynamical point-like impurities oscillating with a frequency Ω can be expressed, in first order of perturbation theory, in terms of the dc current for a set of quasi-static impurities ($\omega_0 \gg \Omega > 1/\tau_{meas}$, with τ_{meas} being the measuring or the relaxation time),

$$I_{dc} = \frac{1}{2}[I_{qst}(\omega_0 + \Omega) + I_{qst}(\omega_0 - \Omega)], \tag{37}$$

or static impurities ($1/\tau_{meas} \gg \Omega$)

$$I_{dc} = \frac{1}{4}[I_{st}(\omega_0 + \Omega) + I_{st}(\omega_0 - \Omega)], \tag{38}$$

with

$$\begin{aligned} I_{st}(\omega_0) = -e \int\int dx_1 dx_2 W(x_1) W(x_2) \\ \cos[2k_F(x_1 - x_2)] H_g(\omega_0, |x_1 - x_2|, T = 0). \qquad (39) \end{aligned}$$

The function H_g is defined as

$$H_g(\omega, x, T = 0) \equiv \frac{\sin(\pi g)}{\pi^2} \int_{|x|}^{\infty} d\tau \frac{\sin(\omega \tau)}{|\tau^2 - x^2|^g} \tag{40}$$

and after explicit evaluation it reads

$$H_g(\omega, x, T = 0) = \mathrm{sgn}(\omega) \frac{J_{g-1/2}(x\omega)}{2^{1/2+g}\sqrt{\pi}\Gamma(g)} \left| \frac{\omega}{x} \right|^{g-1/2}, \tag{41}$$

where $J_\alpha(x)$ are Bessel functions of the first kind and $\Gamma(g)$ is the gamma function.

This result may be readily generalized for the situation where a phase shift of the form $W(x,t) = W(x)\cos(\Omega t + 2Kx)$ is present along an extended impurity. Then we can again write the dc component of the current as

$$I_{dc} = \frac{1}{4}[I_{st,k_F+K}(\omega_0 + \Omega) + I_{st,k_F-K}(\omega_0 - \Omega)], \tag{42}$$

where the channels $\omega_0 + \Omega$ and $\omega_0 - \Omega$ have an "effective" Fermi level at the momentum $k_F + K$ and $k_F - K$, respectively. This means that it is possible to decrease the "effective" Fermi momentum for the $\omega_0 - \Omega$ channel. For simplicity we assume $K = 0$ in the following.

We discussed until now the $T = 0$ case. When the temperature is nonzero, the Green's function is modified by a conformal transformation[22]

$$|\tau^2 - x^2|^g \to \frac{|\sinh[\pi T(\tau - x)] \sinh[\pi T(\tau + x)]|^g}{(\pi T)^{2g}}. \tag{43}$$

Consequently, the function H_g acquires the form

$$H_g(\omega, x, T) \equiv \int_{|x|}^{\infty} \frac{d\tau \sin(\pi g) \sin(\omega \tau) T^{2g} \pi^{2g-2}}{|\sinh[\pi T(\tau - x)] \sinh[\pi T(\tau + x)]|^g}. \tag{44}$$

It is worth noting here that the function $I_{st}(\omega_0)$, defined by Eq. (39), can be represented as a product of a dimensional factor(which actually becomes dimensional only after including the cutoff of the model) and a function of dimensionless variables. The dimensionless part remains invariant with scaling

$$\begin{aligned} \omega_0 \to \omega_0' = \omega_0 \zeta, \quad x \to x' = x/\zeta, \\ W \to W' = W\zeta, \quad T \to T' = T\zeta, \end{aligned} \tag{45}$$

whereas the currents I_{st} and I_{dc} scale as the dimensional factor

$$\begin{aligned} I_{st} &\to I_{st}' \\ I_{st}'[W'(x')](\omega_0', T') &= \zeta^{2g-1} I_{st}[W(x)](\omega_0, T). \end{aligned} \tag{46}$$

These equations set the relation between currents corresponding to different potentials, which have the same shape but a different length parameter. For example, all rectangular-like potentials have the same backscattering current dependence up to the scaling (45). This leads us to the conclusion that it is enough to consider some potential with a fixed length parameter to obtain the

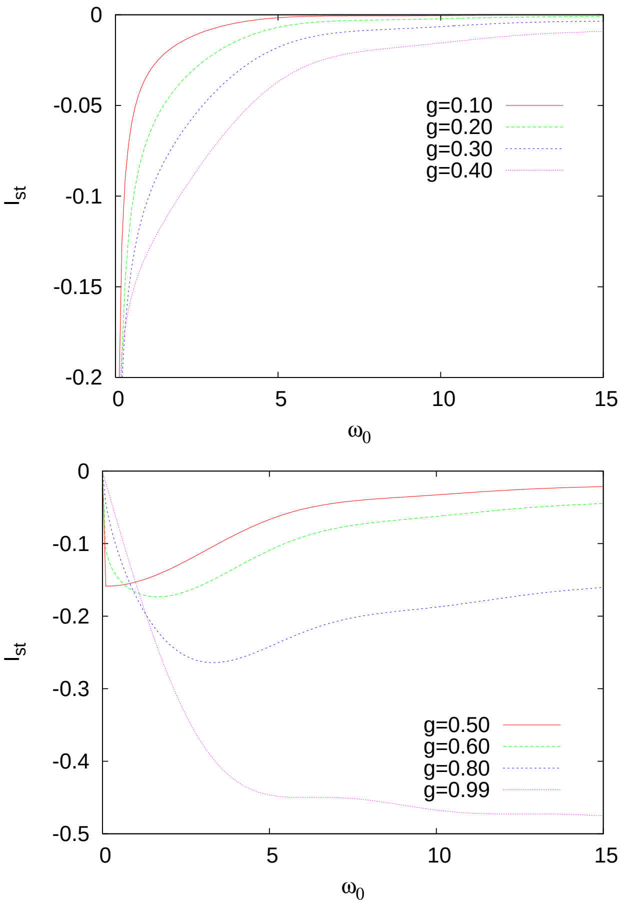

Figure 2: (color online) Dimensionless "static" current I_{st} versus ω_0 for $k_F = 0$ and $W = L = 1$. Upper panel: $g < 1/2$. Lower panel: $g \geq 1/2$.

backscattering current dependence for all potentials of the same form (in lowest order of perturbation theory).

In the case of a potential $W(x)$ with a rectangular shape, the above integral Eq. (39) simplifies to

$$I_{st}(\omega_0) = -eW^2 \int_{-L/2}^{L/2} \int_{-L/2}^{L/2} dx_1 dx_2 \cos[2k_F(x_1 - x_2)] \, H_g(\omega_0, |x_1 - x_2|, T).$$

By changing the variables $x = x_1 - x_2$ and $y = x_1 + x_2$, one integration can be performed, finally yielding

$$I_{st}(\omega_0) = -2eW^2 \int_0^L dx (L - x) \cos(2k_F x) H_g(\omega_0, x, T). \tag{47}$$

In Fig. 2, the dimensionless current in the presence of a static impurity, given by Eq. (47), is plotted for $k_F = 0$, $W = L = 1$, since, as it was argued before, we can fix the length of the barrier without loss of generality. The upper panel shows that for $g < 1/2$, I_{st} always increases, analogous to the case of a point-like impurity. On the other hand, for $g > 1/2$, a non-monotonic behavior of the current appears. As we will discuss later, this non-monotonic behavior may lead to an increase of the conductance, beyond the value G_0.

Let us now discuss the dependence of the current on the value of k_F. To demonstrate the influence of the Fermi momentum, k_F, on the backscattering current off a static impurity, we plot I_{st} versus the Josephson frequency for several values of the Fermi momentum in Fig. 3. It can be promptly observed that the qualitative features are the same for zero and finite k_F, the only effect of the latter is to shift the minimum of the curve to higher values of ω_0.

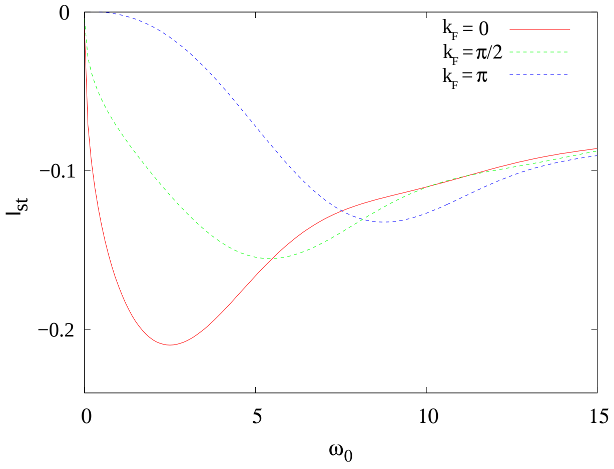

Figure 3: (color online) Dimensionless I_{st} versus ω_0 for $g = 0.7$ and $L = 1$

For future purposes it is worth noting that for the rectangular potential with $k_F = 0$ the following relation holds

$$\frac{\partial^2}{\partial L^2} I_{st} = -2eW^2 H_g(\omega_0, L, T). \tag{48}$$

Eq. (48) is a consequence of a more general relation, valid for an arbitrary static potential[24]

$$\frac{\delta^2}{\delta W(x_1) \delta W(x_2)} I_{st}|_{W=0} = -2e \cos[2k_F(x_1 - x_2)] H_g(\omega_0, |x_1 - x_2|, T).$$

B. Noninteracting electrons $g = 1$ within perturbation theory

Now we can compare this result with the one obtained in Sec. II B using the Büttiker-Landauer formalism by taking the limit $g \to 1$ in Eq. (40). Defining $h(\tau) \equiv \sin(\omega\tau)$, $f(\tau) \equiv |\tau^2 - x^2|$, and $g = 1 - \epsilon$, we may use the formula

$$\lim_{\epsilon \to 0+} \int_x^y d\tau h(\tau) [f(\tau)]^{\epsilon - 1} \epsilon = \frac{h(x)}{f'(x)}, \quad y > x, \tag{49}$$

which holds for a function f with the properties $f(x)=0$ and $f'(x)>0$, yielding

$$H_1(\omega_0,x,T)=T\frac{\sin(\omega_0 x)}{\sinh(2T\pi x)}. \qquad (50)$$

In the case of a rectangular potential and $k_F=0$, we may substitute Eq. (50) into Eq. (47) to obtain

$$I_{st}(\omega_0)=-2eW^2T\int_0^L dx(L-x)\frac{\sin(\omega_0 x)}{\sinh(2T\pi x)}, \qquad (51)$$

which, in the limit $T\to 0$, becomes

$$I_{st}(\omega_0)=-\frac{eW^2}{\pi}\int_0^L dx(L-x)\frac{\sin(\omega_0 x)}{x}. \qquad (52)$$

After integrating by parts and using that $\frac{d}{dy}[2\sin^2(y/2)]=\sin(y)$, we find

$$I_{st}=-\frac{2eW^2L}{\pi}\int_0^{L\omega_0} dy\frac{\sin^2(y/2)}{y^2}, \qquad (53)$$

which exactly coincides with Eq. (23) found in the previous section.

To demonstrate the equivalence between the results obtained using different approaches in the case of nonzero temperature, we note that the second derivative of the currents given by Eqs. (22) and (51) actually coincide,

$$\frac{\partial^2}{\partial L^2}I_{st}=-2eW^2T\frac{\sin(\omega_0 L)}{\sinh(2\pi TL)}. \qquad (54)$$

Therefore, these currents can only differ by a function $F(L,\omega_0,T)=C_1(\omega_0,T)L+C_2(\omega_0,T)$, with C_1 and C_2 being arbitrary functions of their arguments. It follows from $\frac{\partial}{\partial L}I_{st}(L=0,\omega_0,T)=I_{st}(L=0,\omega_0,T)=0$, that $F(L,\omega_0,T)=0$, and the currents given by Eqs. (22) and (51) are thus equal. The same arguments hold also for the case of an arbitrary potential and $k_F\neq 0$, where the equations have similar form, only with the partial derivative replaced by the functional one, $\frac{\partial}{\partial L}\to\frac{\delta}{\delta W(x)}$.

C. One oscillating extended impurity

We can now fix the width of the impurity to be $L=1$ without loss of generality, since the other cases are obtained from the latter by the scaling relation (45). The function $I_{st}(\omega)$ is odd, $I_{st}(-\omega)=-I_{st}(\omega)$, because there is no ratchet effect present in the lowest order of perturbation expansion.[23] The current for the dynamical impurity I_{dc}, according to Eq. (38), reads

$$I_{dc}=\frac{1}{4}[I_{st}(\Omega+\omega_0)-I_{st}(\Omega-\omega_0)]. \qquad (55)$$

Since $I_{st}(\omega_0)$ is always negative or zero for $\omega_0>0$, the function I_{dc} is also negative if both $\omega_0+\Omega$ and $\omega_0-\Omega$ are positive. To obtain a positive backscattering current it is therefore necessary to have $\Omega>\omega_0$, i.e., the frequency of the impurity should be larger than the external bias frequency. Then for small ω_0

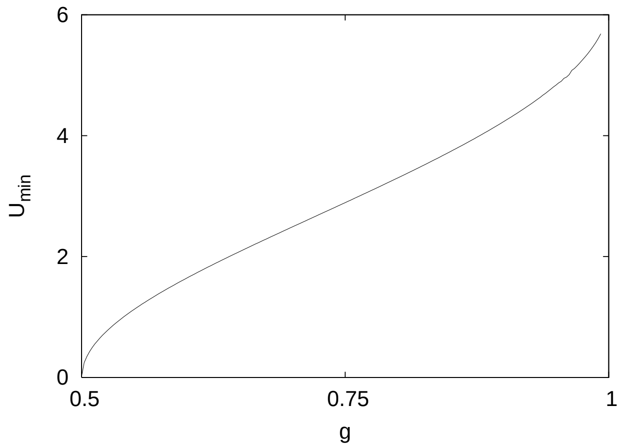

Figure 4: $\omega_{min}L$ versus g.

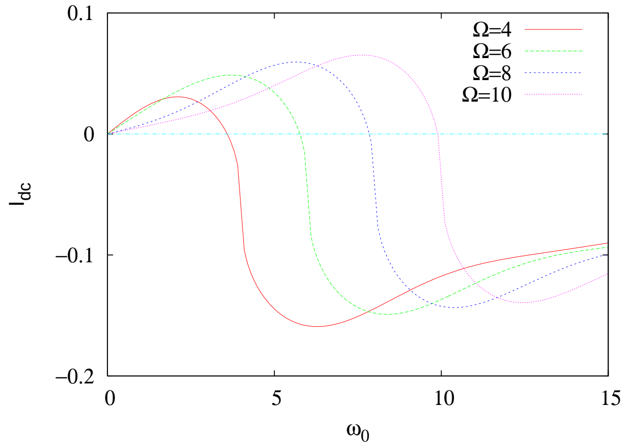

Figure 5: (color online) I_{dc} versus ω_0 for $g=0.7$.

$$I_{dc}=\frac{1}{2}I'_{st}(\Omega)\omega_0 \qquad (56)$$

and therefore, the I_{dc} current is positive if $I'_{st}(\Omega)>0$, at least for small ω_0. Let us begin by considering the current in the region $1/2<g<1$. For a fixed value of the interaction parameter g within this region, the "static" current $I_{st}(\omega_0)$ continuously decreases from zero, for $\omega_0=0$, to a minimal value $I_{st}(\omega_{min})$, and then in the remaining region it increases, see Fig. (3). Let us concentrate in the following on the example with $k_F=0$, which provides a lower bound for ω_{min}. The value of $\omega_{min}L$ then depends only on the interaction strength g, and it changes monotonously from 0 at $g=1/2$ to 5 at $g\approx 0.95$, but then diverges to $+\infty$ when $g\to 1$, see Fig. (4). Therefore, for typical values of g, $\omega_{min}L$ is of order 1. Note that the minimum is very sensitive to the impurity length, and never achievable for the case of a point-like impurity ($L \to 0$), for which $I_{st}(\omega_0)$ is a monotonously decreasing function. Since in our case the backscattering current changes sign only when $I'_{st}(\Omega) > 0$, we have to choose $\Omega > \omega_{min}$ in order to obtain an increase of the dc current, see Eq. (56) and Fig. (3). Now, considering I_{dc} as a function of the applied voltage V for some fixed $\Omega > \omega_{min}$, one finds that the dc current is positive in a region $0 < \omega_0 < \omega_0^*(\Omega)$, see Fig. (5). Therefore, the effect of current enhancement in the region $1/2 < g < 1$ occurs only if the frequency of the impurity is larger than some minimal value ω_{min}, which depends on g. For the frequency $\Omega > \omega_{min}$, the continuous function I_{dc} is then positive within a region $0 < \omega_0 < \omega_0^*$.

IV. CONCLUSIONS

In this work we calculated the backscattering current off extended impurities in a Luttinger liquid. We started our analysis by considering noninteracting electrons ($g = 1$) scattered by a rectungular-like barrier of width L and height W. In this simplified case the problem can be exactly solved using the Büttiker-Landauer formalism. We evaluate the backscattering current at finite and zero temperatures for the Fermi momentum $k_F = 0$, and find that for small Josephson frequencies $L\omega_0 < 2$ the result is almost indistinguishable from the backscattering current off a point-like impurity represented by a barrier $\tilde{W}(x) = WL\delta(x)$. In the region $L\omega_0 > 2$ these currents differ considerably, since in the case of a point-like impurity the current decreases linearly whereas for the extended barrier it saturates at the value $I_{bs} = -eW^2L/2$. We also calculated the backscattering current off a weak backscattering potential with an arbitrary shape in lowest order of perturbation expansion.

The effect of a time-dependent extended barrier, $W(x,t)$, in the presence of repulsive electron-electron interactions was then considered. Using the bosonization technique combined with the Keldysh formalism, we showed that the backscattering current off dynamical impurities can be expressed in terms of the backscattering current off static ones. It actually turns out that the only effect of the barrier oscillating with a frequency Ω is to split the conduction channel ω_0 into two channels, $\omega_0 \pm \Omega$. We then evaluated the backscattering current off static barriers $I_{st}(\omega_0)$ and showed that it is a non-monotonic function of ω_0, which for $1/2 < g < 1$ has a minimum at ω_{min}. In addition, we observed that ω_{min} depends on the interaction strength and the parameter $k_F L$, with $k_F = 0$ providing a lower bound for ω_{min}. Therefore, by choosing Ω such that $\Omega > \omega_{min}$, it may occur that the backscattering current changes sign and in a certain region of applied voltage $0 < \omega_0 < \omega_0^*$ the conductance will be greater than the quantum of conductance G_0. The phenomenon of the conductance enhancement may occur in the presence of oscillating impurities as well, but the main difference concerns the region of parameters where it appears, which depends on the type of the barrier. In the case of a single point-like oscillating barrier it only occurs for strongly repulsive interactions $0 < g < 1/2$,[12] whereas for two or more point-like barriers it may happen in the entire range of repulsive interactions $0 < g < 1$ if the barriers oscillate with the same frequency Ω.[14] On the other hand, if the barrier is extended, the phenomenon already appears for *a single* oscillating barrier in the entire region of the repulsive electron-electron interactions ($0 < g < 1$). The interval of voltage where the conductance increases can be optimally chosen by adjusting the frequency Ω of the oscillating barrier.

In summary, we investigated the transport properties of a Luttinger liquid accounting for the most general case of scattering off extended time-dependent barriers and determined the values od parameters where the conductance may increase beyond its quantized value.

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Appendix A

The matrix M for a single extended impurity can also be found in a different approach, using elements of the Lie group theory. Considering the extended impurity as a set of infinitely narrow impurities, the matrix M may be represented as an infinite product of the matrices corresponding to the scattering by the individual impurities. The transmission matrix corresponding to a vanishingly narrow potential (Eq. (5) with $L \to 0$) is given by

$$M = I + i\mathcal{T}\Delta L, \tag{A1}$$

where I is the 2×2 unity matrix, and $\Delta L \to 0$ is the width of the impurity barrier. This means that $\Delta\psi(x) \equiv \psi(x+\Delta L/2) - \psi(x-\Delta L/2) = i\mathcal{T}\psi(x)\Delta L$, and the matrix $\mathcal{T}$ is obtained from the equations of motion (3),

$$\mathcal{T} = \begin{pmatrix} \omega & -W \\ W & -\omega \end{pmatrix}. \tag{A2}$$

Therefore, we can write the transmission matrix as $M = e^{i\sigma_a \xi^a}$, where σ_a are the Pauli matrices and $\xi^1 = 0$, $\xi^2 = -iW\Delta L$, $\xi^3 = \omega\Delta L$. Since the backscattering potential $W(x)$ is constant for $-L/2 < x < L/2$, the transmission matrices of vanishingly narrow impurities commute with each other, which allows us to find parameters ξ^a for a rectangular potential with a finite length $L > 0$ in the form $\xi^1 = 0$, $\xi^2 = -iWL$, and $\xi^3 = \omega L$. On the other hand,

$$e^{i\sigma_a \xi^a} = \begin{pmatrix} \cos(\xi) + i\frac{\xi^3}{\xi}\sin(\xi) & \frac{i\xi^1 + \xi^2}{\xi}\sin(\xi) \\ \frac{i\xi^1 - \xi^2}{\xi}\sin(\xi) & \cos(\xi) - i\frac{\xi^3}{\xi}\sin(\xi) \end{pmatrix},$$

where $\xi \equiv \sqrt{(\xi^1)^2 + (\xi^2)^2 + (\xi^3)^2}$. Therefore, $\xi = kL$ and we obtain Eq. (13).

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